

# MOSFET – Power, Single, P-Channel, Trench, SC-88 -20 V, -4.2 A

## NTJS4151P

### Features

- Leading Trench Technology for Low  $R_{DS(on)}$  Extending Battery Life
- SC-88 Small Outline (2x2 mm) for Maximum Circuit Board Utilization, Same as SC-70-6
- Gate Diodes for ESD Protection
- Pb-Free Package is Available

### Applications

- High Side Load Switch
- Cell Phones, Computing, Digital Cameras, MP3s and PDAs

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise stated)

| Parameter                                                         |                        |                               | Symbol         | Value      | Unit             |
|-------------------------------------------------------------------|------------------------|-------------------------------|----------------|------------|------------------|
| Drain-to-Source Voltage                                           |                        |                               | $V_{DS}$       | -20        | V                |
| Gate-to-Source Voltage                                            |                        |                               | $V_{GS}$       | $\pm 12$   | V                |
| Continuous Drain Current (Note 1)                                 | Steady State           | $T_A = 25^\circ\text{C}$      | $I_D$          | -3.3       | A                |
|                                                                   |                        | $T_A = 85^\circ\text{C}$      |                | -2.4       |                  |
|                                                                   | $t \leq 5\text{ s}$    | $T_A = 25^\circ\text{C}$      |                | -4.2       |                  |
| Power Dissipation (Note 1)                                        | Steady State           | $T_A = 25^\circ\text{C}$      | $P_D$          | 1.0        | W                |
| Pulsed Drain Current                                              |                        | $t_p = 10\text{ }\mu\text{s}$ | $I_{DM}$       | -10        | A                |
| Operating Junction and Storage Temperature                        |                        |                               | $T_J, T_{STG}$ | -55 to 150 | $^\circ\text{C}$ |
| Source Current (Body Diode)                                       |                        |                               | $I_S$          | -1.3       | A                |
| Lead Temperature for Soldering Purposes (1/8" from case for 10 s) |                        |                               | $T_L$          | 260        | $^\circ\text{C}$ |
| ESD                                                               | Human Body Model (HBM) |                               | ESD            | 4000       | V                |

### THERMAL RESISTANCE RATINGS (Note 1)

| Parameter                                 | Symbol          | Max | Unit               |
|-------------------------------------------|-----------------|-----|--------------------|
| Junction-to-Ambient – Steady State        | $R_{\theta JA}$ | 125 | $^\circ\text{C/W}$ |
| Junction-to-Ambient – $t \leq 5\text{ s}$ | $R_{\theta JA}$ | 75  |                    |
| Junction-to-Lead – Steady State           | $R_{\theta JL}$ | 45  |                    |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

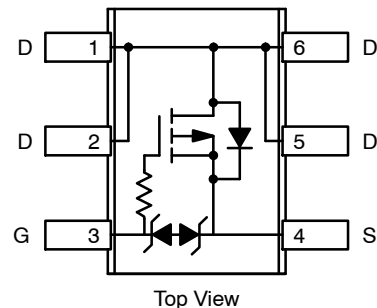


ON Semiconductor®

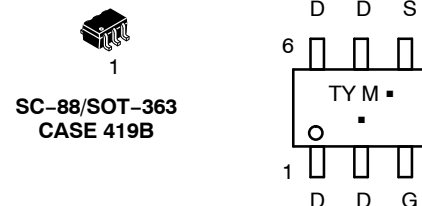
<http://onsemi.com>

| $V_{(BR)DS}$ | $R_{DS(on)}$ Typ        | $I_D$ Max |
|--------------|-------------------------|-----------|
| -20 V        | 47 m $\Omega$ @ -4.5 V  | -4.2 A    |
|              | 70 m $\Omega$ @ -2.5 V  |           |
|              | 180 m $\Omega$ @ -1.8 V |           |

### SC-88 (SOT-363)



### MARKING DIAGRAM & PIN ASSIGNMENT



TY = Device Code  
M = Date Code  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

See detailed ordering and shipping information on page 4 of this data sheet.

# NTJS4151P

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub>=25°C unless otherwise stated)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|-----------|--------|----------------|-----|-----|-----|------|
|-----------|--------|----------------|-----|-----|-----|------|

### OFF CHARACTERISTICS

|                                                           |                                      |                                                 |                       |     |      |       |
|-----------------------------------------------------------|--------------------------------------|-------------------------------------------------|-----------------------|-----|------|-------|
| Drain-to-Source Breakdown Voltage                         | V <sub>(BR)DSS</sub>                 | V <sub>GS</sub> = 0 V, I <sub>D</sub> = -250 μA | -20                   |     |      | V     |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | V <sub>(BR)DSS</sub> /T <sub>J</sub> |                                                 |                       | -12 |      | mV/°C |
| Zero Gate Voltage Drain Current                           | I <sub>DSS</sub>                     | V <sub>GS</sub> = 0 V, V <sub>DS</sub> = -16 V  | T <sub>J</sub> = 25°C |     | -1.0 | μA    |
|                                                           |                                      |                                                 | T <sub>J</sub> = 85°C |     | -5.0 | μA    |
| Gate-to-Source Leakage Current                            | I <sub>GSS</sub>                     | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±4.5 V |                       |     | ±1.5 | μA    |
|                                                           |                                      | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±12 V  |                       |     | ±10  | mA    |

### ON CHARACTERISTICS (Note 2)

|                                            |                                     |                                                              |       |     |      |       |
|--------------------------------------------|-------------------------------------|--------------------------------------------------------------|-------|-----|------|-------|
| Gate Threshold Voltage                     | V <sub>GS(TH)</sub>                 | V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = -250 μA | -0.40 |     | -1.2 | V     |
| Negative Threshold Temperature Coefficient | V <sub>GS(TH)</sub> /T <sub>J</sub> |                                                              |       | 4.0 |      | mV/°C |
| Drain-to-Source On Resistance              | R <sub>DS(on)</sub>                 | V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -3.3 A            |       | 47  | 60   | mΩ    |
|                                            |                                     | V <sub>GS</sub> = -2.5 V, I <sub>D</sub> = -2.3 A            |       | 70  | 85   |       |
|                                            |                                     | V <sub>GS</sub> = -1.8 V, I <sub>D</sub> = -1.0 A            |       | 180 | 205  |       |
| Forward Transconductance                   | g <sub>FS</sub>                     | V <sub>GS</sub> = -10 V, I <sub>D</sub> = -3.3 A             |       | 12  |      | S     |

### CHARGES AND CAPACITANCES

|                              |                     |                                                                            |  |     |  |    |
|------------------------------|---------------------|----------------------------------------------------------------------------|--|-----|--|----|
| Input Capacitance            | C <sub>ISS</sub>    | V <sub>GS</sub> = 0 V, f = 1.0 MHz, V <sub>DS</sub> = -10 V                |  | 850 |  | pF |
| Output Capacitance           | C <sub>OSS</sub>    |                                                                            |  | 160 |  |    |
| Reverse Transfer Capacitance | C <sub>RSS</sub>    |                                                                            |  | 110 |  |    |
| Total Gate Charge            | Q <sub>G(TOT)</sub> | V <sub>GS</sub> = -4.5 V, V <sub>DS</sub> = -10 V, I <sub>D</sub> = -3.3 A |  | 10  |  | nC |
| Gate-to-Source Charge        | Q <sub>GS</sub>     |                                                                            |  | 1.5 |  |    |
| Gate-to-Drain Charge         | Q <sub>GD</sub>     |                                                                            |  | 2.8 |  |    |

### SWITCHING CHARACTERISTICS (Note 3)

|                     |                     |                                                                                                    |  |      |  |    |
|---------------------|---------------------|----------------------------------------------------------------------------------------------------|--|------|--|----|
| Turn-On Delay Time  | t <sub>d(ON)</sub>  | V <sub>GS</sub> = -4.5 V, V <sub>DD</sub> = -10 V, I <sub>D</sub> = -1.0 A, R <sub>G</sub> = 6.0 Ω |  | 0.85 |  | μs |
| Rise Time           | t <sub>r</sub>      |                                                                                                    |  | 1.7  |  |    |
| Turn-Off Delay Time | t <sub>d(OFF)</sub> |                                                                                                    |  | 2.7  |  |    |
| Fall Time           | t <sub>f</sub>      |                                                                                                    |  | 4.2  |  |    |

### DRAIN-SOURCE DIODE CHARACTERISTICS

|                         |                 |                                                                                |  |       |      |    |
|-------------------------|-----------------|--------------------------------------------------------------------------------|--|-------|------|----|
| Forward Diode Voltage   | V <sub>SD</sub> | V <sub>GS</sub> = 0 V, I <sub>S</sub> = -1.3 A, T <sub>J</sub> = 25°C          |  | -0.75 | -1.2 | V  |
| Reverse Recovery Time   | t <sub>RR</sub> | V <sub>GS</sub> = 0 V, dI <sub>S</sub> /dt = 100 A/μs, I <sub>S</sub> = -1.3 A |  | 63    |      | ns |
| Charge Time             | T <sub>a</sub>  |                                                                                |  | 9.0   |      |    |
| Discharge Time          | T <sub>b</sub>  |                                                                                |  | 54    |      |    |
| Reverse Recovery Charge | Q <sub>RR</sub> |                                                                                |  | 0.23  |      | nC |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

3. Switching characteristics are independent of operating junction temperatures.

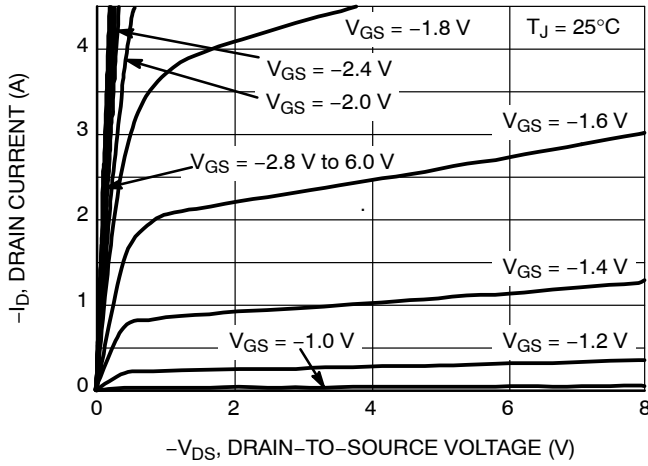


Figure 1. On-Region Characteristics

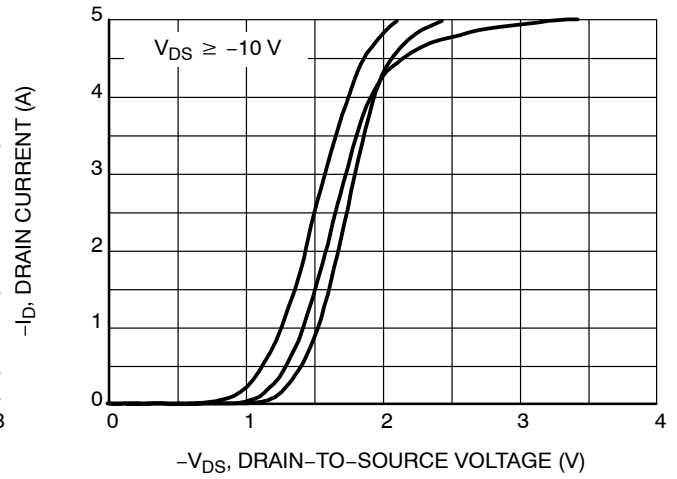


Figure 2. On-Region Characteristics

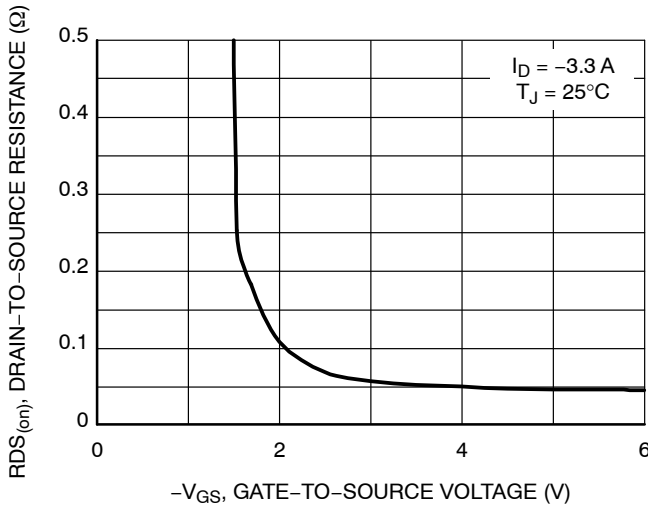


Figure 3. On-Resistance versus Gate-to-Source Voltage

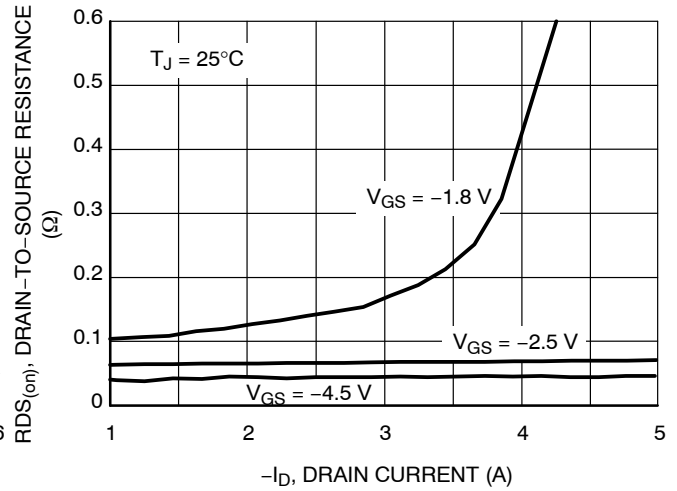


Figure 4. On-Resistance versus Drain Current and Gate Voltage

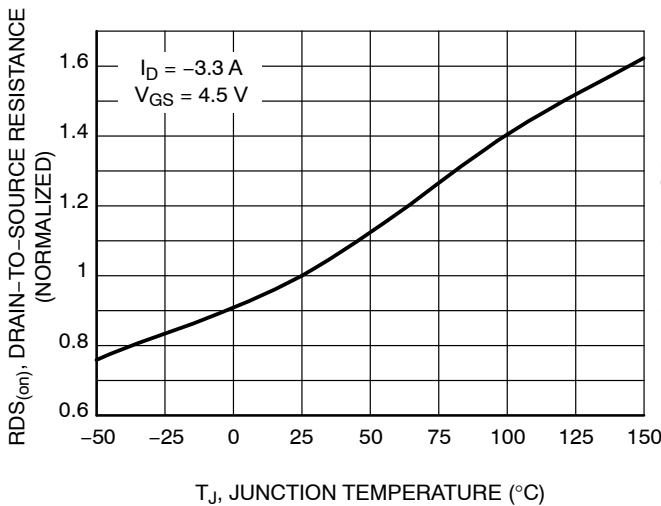


Figure 5. On-Resistance Variation with Temperature

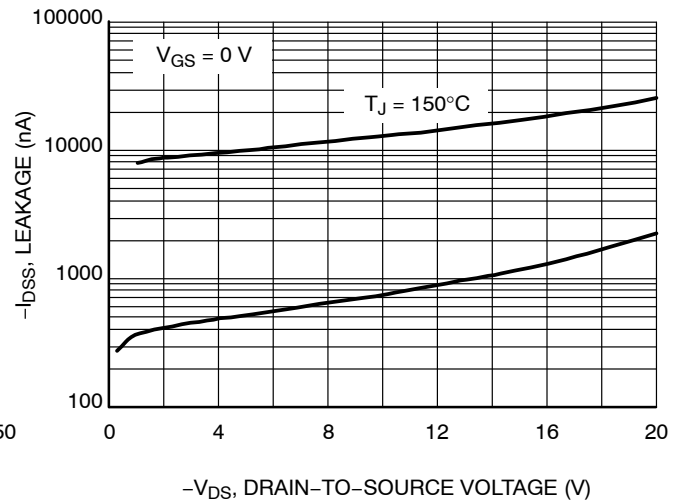


Figure 6. Drain-to-Source Leakage Current versus Voltage

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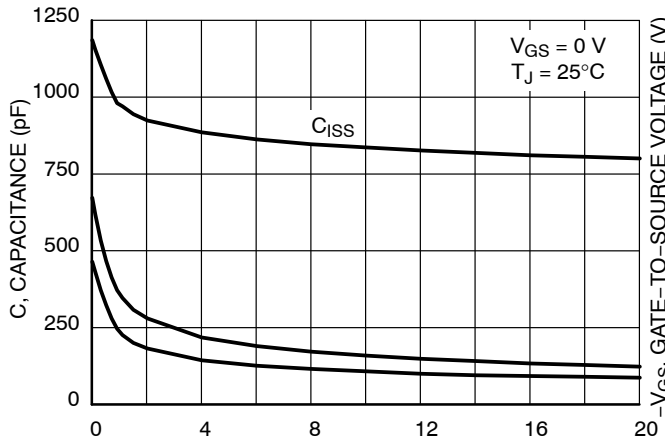


Figure 7. Capacitance Variation

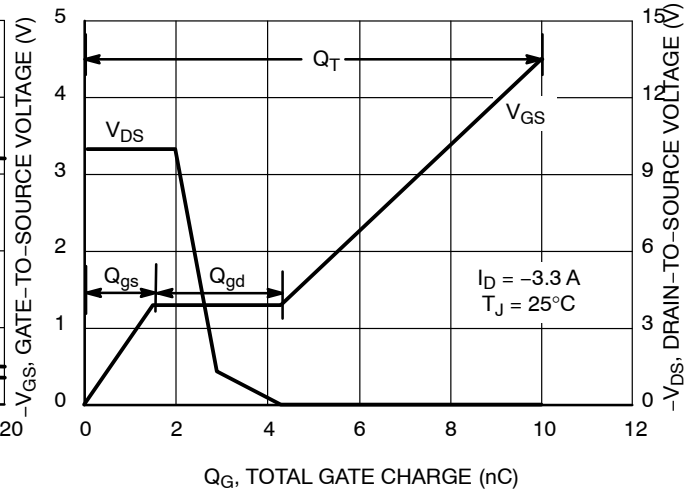


Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Charge

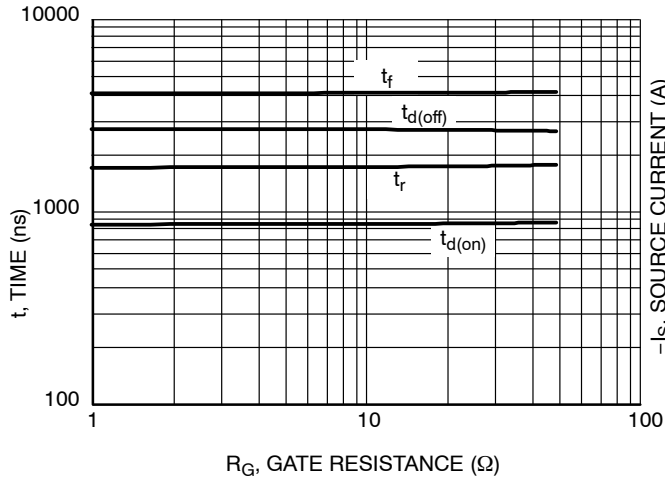


Figure 9. Resistive Switching Time Variation Gate Resistance

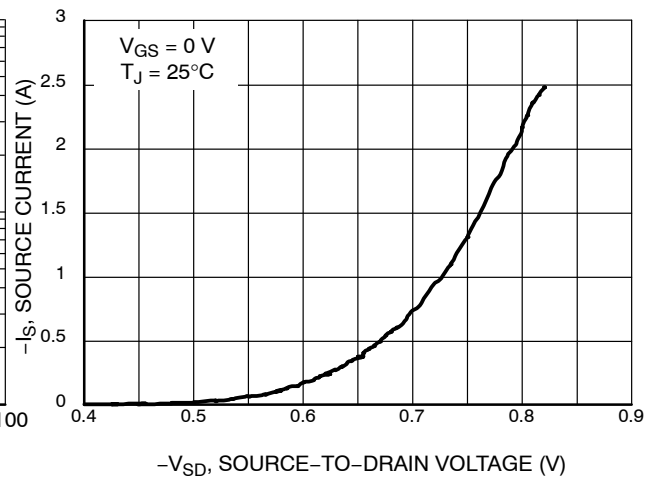


Figure 10. Diode Forward Voltage versus Current

Table 1. ORDERING INFORMATION

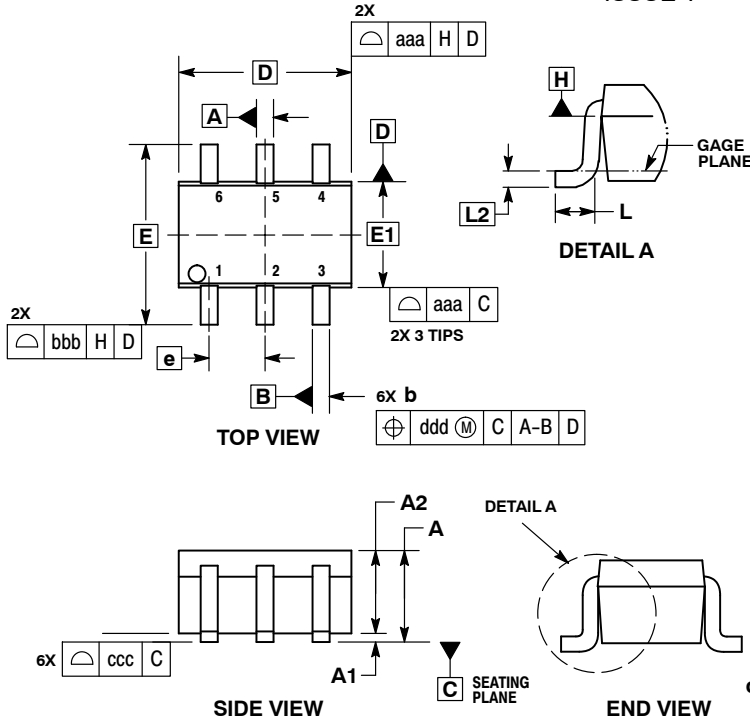
| Part Number  | Marking (XX) | Package         | Shipping†          |
|--------------|--------------|-----------------|--------------------|
| NTJS4151PT1  | TY           | SC-88           | 3000 / Tape & Reel |
| NTJS4151PT1G | TY           | SC-88 (Pb-Free) | 3000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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## PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363  
CASE 419B-02  
ISSUE Y

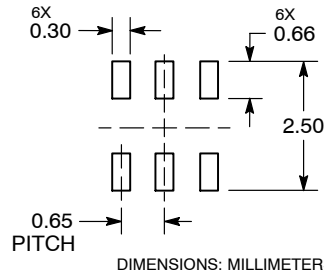


### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

| DIM | MILLIMETERS |      |      | INCHES    |       |       |
|-----|-------------|------|------|-----------|-------|-------|
|     | MIN         | NOM  | MAX  | MIN       | NOM   | MAX   |
| A   | ---         | ---  | 1.10 | ---       | ---   | 0.043 |
| A1  | 0.00        | ---  | 0.10 | 0.000     | ---   | 0.004 |
| A2  | 0.70        | 0.90 | 1.00 | 0.027     | 0.035 | 0.039 |
| b   | 0.15        | 0.20 | 0.25 | 0.006     | 0.008 | 0.010 |
| C   | 0.08        | 0.15 | 0.22 | 0.003     | 0.006 | 0.009 |
| D   | 1.80        | 2.00 | 2.20 | 0.070     | 0.078 | 0.086 |
| E   | 2.00        | 2.10 | 2.20 | 0.078     | 0.082 | 0.086 |
| E1  | 1.15        | 1.25 | 1.35 | 0.045     | 0.049 | 0.053 |
| e   | 0.65 BSC    |      |      | 0.026 BSC |       |       |
| L   | 0.26        | 0.36 | 0.46 | 0.010     | 0.014 | 0.018 |
| L2  | 0.15 BSC    |      |      | 0.006 BSC |       |       |
| aaa | 0.15        |      |      | 0.006     |       |       |
| bbb | 0.30        |      |      | 0.012     |       |       |
| ccc | 0.10        |      |      | 0.004     |       |       |
| ddd | 0.10        |      |      | 0.004     |       |       |

### RECOMMENDED SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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